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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of Robert J. Falster
Serial No. 10/038,084
Filed January 03, 2002
Confirmation No. 7363

Art Unit 2814

For SILICON ON INSULATOR STRUCTURE HAVING A LOW DEFECT DENSITY
DEVICE LAYER AND A PROCESS FOR THE PREPARATION THEREOF

Examiner Anh D. Mai

August 27, 2004

AMENDMENT D

TO THE COMMISSIONER FOR PATENTS,

SIR:

In response to Telephone Interview of today, August 27, 2004, please consider the following amendments and remarks:

Amendments begin on page 2 of this paper,

Remarks/Arguments begin on page 5 of this paper.

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Applicant's Name: Robert J. Falster

Serial No. (Control No.): 10/038,084 Examiner: Mai

Filing Date: January 03, 2002 Art Unit: 2814

Application Title: SILICON ON INSULATOR STRUCTURE HAVING A LOW
DEFECT DENSITY DEVICE LAYER AND A PROCESS FOR THE PREPARATION
THEREOF

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